## SCHOTTKY RECTIFIER DIODES 2.6 A AND 30 A
## SCHOTTKY GLEICHRICHTERDIODEN 2,6 A UND 30 A

| Type / Typ | Maximum ratings • Grenzdaten | | | | | Characteristic data • Kenndaten | | | | Case Gehäuse |
|---|---|---|---|---|---|---|---|---|---|---|
| | $I_{FAV}$ | $I_{FSM}$ [3] | $U_{RRM}$ | $U_{RSM}$ [3] | $\vartheta_a$ | $U_F$ max at bei | $I_F$ | $U_R$ min at bei | $I_R$ | |
| | A | A | V | V | °C | V | A | V | mA | |
| **KYS26/30** | 2,6 [1] | 120 | 30 | 35 | —40 ... +125 | 0,6 | 3 | 30 | 5 | D58 |
| **KYS26/40** | 2,6 [1] | 120 | 40 | 45 | —40 ... +125 | 0,6 | 3 | 40 | 5 | D58 |
| **KYS30/30** | 30 [2] | 400 | 30 | 35 | —55 ... +125 | 0,6 | 30 [4] | 30 | 10 | D55/1 |
| **KYS30/40** | 30 [2] | 400 | 40 | 45 | —55 ... +125 | 0,6 | 30 [4] | 40 | 10 | D55/1 |

[1] $R_L$ = R, L; $\theta$ = 180°, $\vartheta_a$ = 25 °C
[2] $R_L$ = R, L; $\theta$ = 180°, $\vartheta_c$ = 95 °C
[3] t ≦ 10 ms
[4] $\vartheta_j$ = 100 °C

## VERY HIGH SPEED RECTIFIER DIODES 25 A
## SEHR SCHNELLE GLEICHRICHTERDIODEN 25 A

| Type / Typ | Maximum ratings • Grenzdaten | | | | | | Characteristic data • Kenndaten | | | | | Case Gehäuse |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| | $I_{FAV}$ [1] | $I_{FRM}$ | $I_{FSM}$ [2] | $U_{RRM}$ | $U_{RSM}$ | $\vartheta_a$ | $U_F$ [3] max at bei | $I_F$ | $I_R$ max at bei | $U_R$ | $t_{rr}$ [4] max | |
| | A | A | A | V | V | °C | V | A | µA | V | ns | |
| **KYW31/50** | 25 | 43 | 300 | 50 | 60 | 155 | 0,85 | 20 | 100 | 50 | 100 | D55 |
| **KYW31/100** | 25 | 43 | 300 | 100 | 120 | 155 | 0,85 | 20 | 100 | 100 | 100 | D55 |
| **KYW31/150** | 25 | 43 | 300 | 150 | 180 | 155 | 0,85 | 20 | 100 | 150 | 100 | D55 |
| **KYW77/50** | 25 | 43 | 500 | 50 | 60 | 155 | 0,85 | 20 | 50 | 50 | 60 | D55/1 |
| **KYW77/100** | 25 | 43 | 500 | 100 | 120 | 155 | 0,85 | 20 | 50 | 100 | 60 | D55/1 |
| **KYW77/150** | 25 | 43 | 500 | 150 | 180 | 155 | 0,85 | 20 | 50 | 150 | 60 | D55/1 |
| **KYW77/200** | 25 | 43 | 500 | 200 | 230 | 155 | 0,85 | 20 | 50 | 200 | 60 | D55/1 |

[1] $\vartheta_c$ = 125 °C, $\theta$ = 180°, $R_L$ = R
[2] t ≦ 10 ms
[3] $\vartheta_j$ = 100 °C
[4] $I_F$ = 1 A → $U_R$ = 30 V, —dI/dt = 50 A/µs

## DIODES FOR SEMICONDUCTOR DEVICES PROTECTION AGAINST IMPULSE OVERVOLTAGE
## DIODEN FÜR HALBLEITERBAUELEMENTE-SCHUTZ GEGEN IMPULS-ÜBERSPANNUNGEN

| Type / Typ | Maximum ratings • Grenzdaten | | | $U_{BR}$ | $U_{CL}$ [2] | $P_{p\ min.}$ | $U_{CL} : U_{BR}$ | $U_{R\ min.}$ | Case Gehäuse |
|---|---|---|---|---|---|---|---|---|---|
| | $I_{FSM}$ [1] | $I_{FM}$ [2] | $P_{tot}$ | ($I_Z$ = 1 mA) | max | ($t_p$ = 1 ms) | [2] | ($I_R$ = 5 µA) | |
| | A | A | W | V | V | W | max. | V | |
| **KZL81/20** | 40 | 400/$U_{CL}$ | 1 | 17—22 | $U_{BR}$ . 1,35 | 400 | 1,35 | 16 | D26 |
| **KZL81/40** | 40 | 400/$U_{CL}$ | 1 | 34—45 | $U_{BR}$ . 1,35 | 400 | 1,35 | 32 | D26 |
| **KZL81/145** | 40 | 400/$U_{CL}$ | 1 | 120—170 | $U_{BR}$ . 1,45 | 400 | 1,45 | 105 | D26 |

[1] t ≦ 10 ms
[2] $P_p$ = 400 W, $t_p$ = 1 ms; $\vartheta_a$ = 25 °C

For all types valid • Für alle Typen gilt:
$U_F$ ≦ 1,1 V at • bei $I_F$ = 1 A, $\vartheta_a$ = 25 °C
Duty cycle of repetitive impulse in reverse direction • Impulspausenverhältnis in Sperr-Richtung:
≦ $1 . 10^{-4}$ at • bei $P_P$ = 400 W
$\vartheta_{j\ max.}$ = 155 °C, $\vartheta_{a\ min.-max.}$ = —55 °C ... +155 °C